

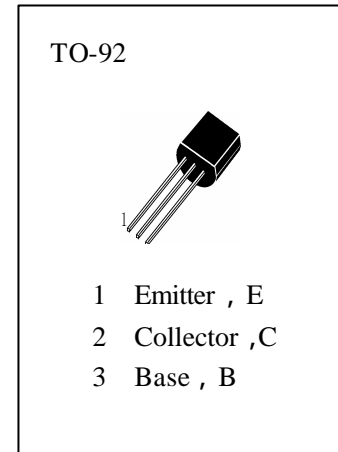


**APPLICATIONS**

The H733 is designed for driver stage of AF amplifier  
And low speed switching.

**ABSOLUTE MAXIMUM RATINGS (  $T_a=25$  )**

- $T_{stg}$ —Storage Temperature..... -55~150
- $T_j$ —Junction Temperature.....150
- $P_C$ —Collector Dissipation.....250mW
- $V_{CBO}$ —Collector-Base Voltage.....-60V
- $V_{CEO}$ —Collector-Emitter Voltage.....-50V
- $V_{EBO}$ —Emitter-Base Voltage.....-5V
- $I_C$ —Collector Current.....-150mA



**ELECTRICAL CHARACTERISTICS (  $T_a=25$  )**

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	-60			V	$I_C=-100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	-50			V	$I_C=-10mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	-5			V	$I_E=-10 \mu A, I_C=0$
HFE	DC Current Gain	90		600		$V_{CE}=-6V, I_C=-1mA$
VCE(sat)	Collector- Emitter Saturation Voltage			-0.3	V	$I_C=-100mA, I_B=-10mA$
VBE(ON)	Base-Emitter On Voltage	-0.5		-0.8	V	$V_{CE}=-6V, I_C=-1mA$
ICBO	Collector Cut-off Current			-100	nA	$V_{CB}=-60V, I_E=0$
IEBO	Emitter Cut-off Current			-100	nA	$V_{EB}=-5V, I_C=0$
ft	Current Gain-Bandwidth Product		180		MHz	$V_{CE}=-6V, I_C=-10mA$
Cob	Output Capacitance		4.5		pF	$V_{CB}=-10V, I_E=0, f=1MHz$

**hFE Classification**

R	Q	P	K
90—180	135—270	200—400	300—600